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Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

ON Semiconductor
2N4401RLRM

For any questions, you can email us directly:
sales@integrated-circuit.com

2N4401

Preferred Device

General Purpose Transistors

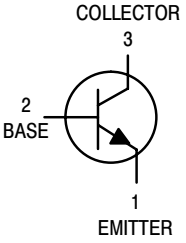
NPN Silicon

ON Semiconductor®

http://onsemi.com

Features

- Pb−Free Packages are Available*



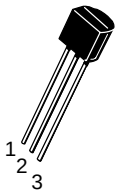
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	40	Vdc
Collector − Base Voltage	V_{CBO}	60	Vdc
Emitter − Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	600	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

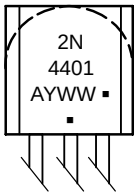
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



TO−92
CASE 29
STYLE 1

MARKING DIAGRAM



2N4401	= Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week
▪	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2N4401

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Breakdown Voltage (Note 1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	−	Vdc
Collector−Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	60	−	Vdc
Emitter−Base Breakdown Voltage (I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	−	Vdc
Base Cutoff Current (V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{BEV}	−	0.1	μAdc
Collector Cutoff Current (V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{CEX}	−	0.1	μAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain	h_{FE}			−
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)		20	−	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)		40	−	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		80	−	
(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)		100	300	
(I_C = 500 mAdc, V_{CE} = 2.0 Vdc)		40	−	
Collector−Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	−	0.4	Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)		−	0.75	
Base−Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	0.75	0.95	Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)		−	1.2	
SMALL−SIGNAL CHARACTERISTICS				
Current−Gain − Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	250	−	MHz
Collector−Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	−	6.5	pF
Emitter−Base Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{eb}	−	30	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	1.0	15	k Ω
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	0.1	8.0	X 10^{-4}
Small−Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	40	500	−
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	1.0	30	μmhos
SWITCHING CHARACTERISTICS				
Delay Time (V_{CC} = 30 Vdc, V_{BE} = 2.0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	−	15	ns
Rise Time	t_r	−	20	ns
Storage Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	−	225	ns
Fall Time	t_f	−	30	ns

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N4401

ORDERING INFORMATION

Device	Package	Shipping†
2N4401	TO−92	5,000 Units / Box
2N4401G	TO−92 (Pb−Free)	5,000 Units / Box
2N4401RLRA	TO−92	2000 / Tape & Reel
2N4401RLRAG	TO−92 (Pb−Free)	2000 / Tape & Reel
2N4401RLRM	TO−92	2000 / Ammo Pack
2N4401RLRMG	TO−92 (Pb−Free)	2000 / Ammo Pack
2N4401RLRP	TO−92	2000 / Ammo Pack
2N4401RLRPG	TO−92 (Pb−Free)	2000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

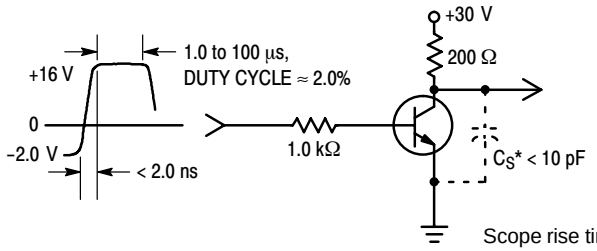


Figure 1. Turn−On Time

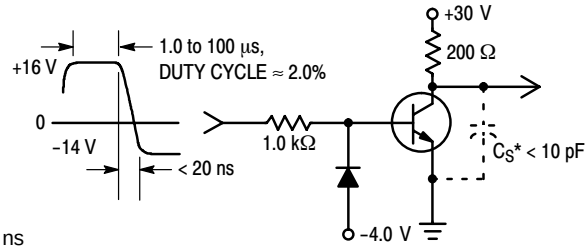


Figure 2. Turn−Off Time

Scope rise time < 4.0 ns
*Total shunt capacitance of test jig connectors, and oscilloscope

TRANSIENT CHARACTERISTICS

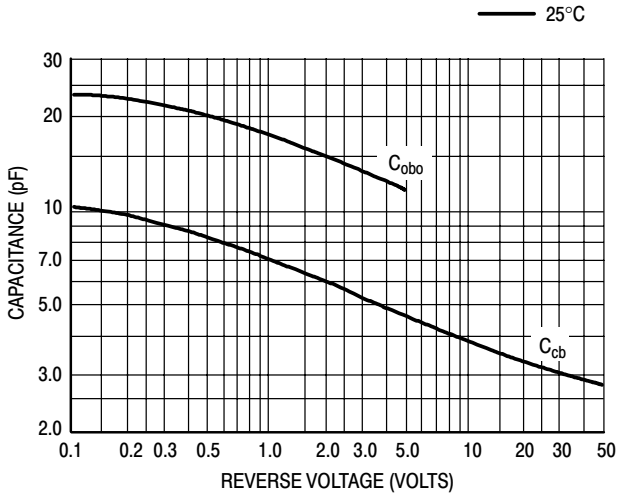


Figure 3. Capacitances

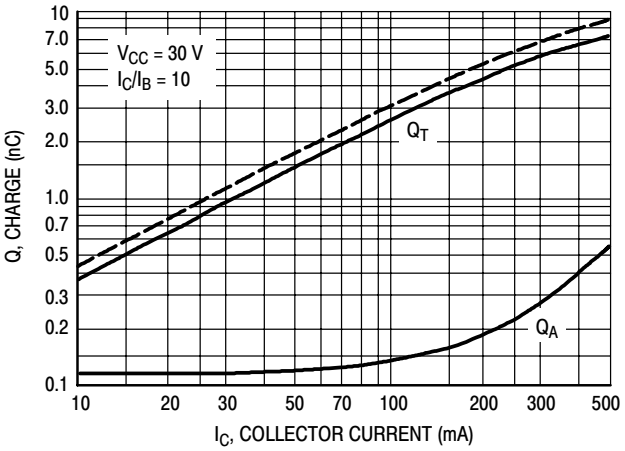


Figure 4. Charge Data

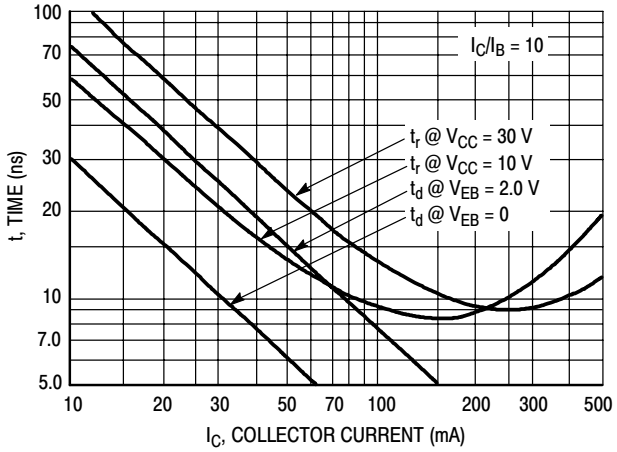


Figure 5. Turn−On Time

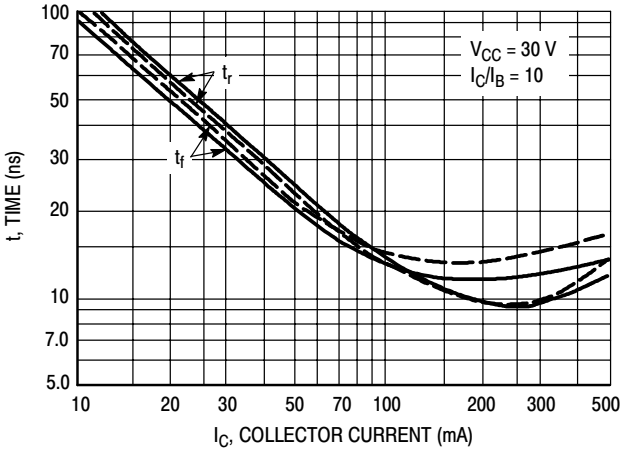


Figure 6. Rise and Fall Times

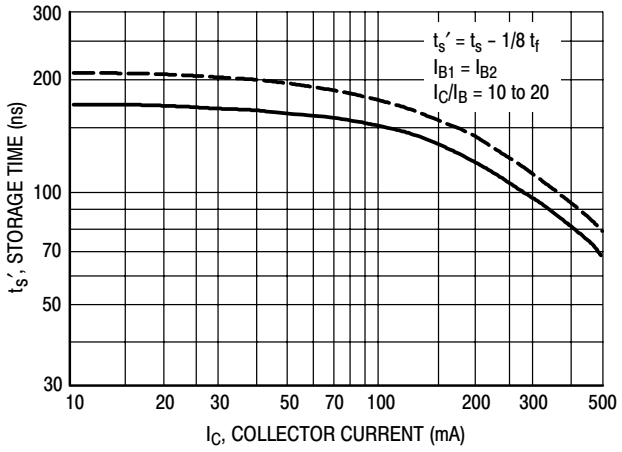


Figure 7. Storage Time

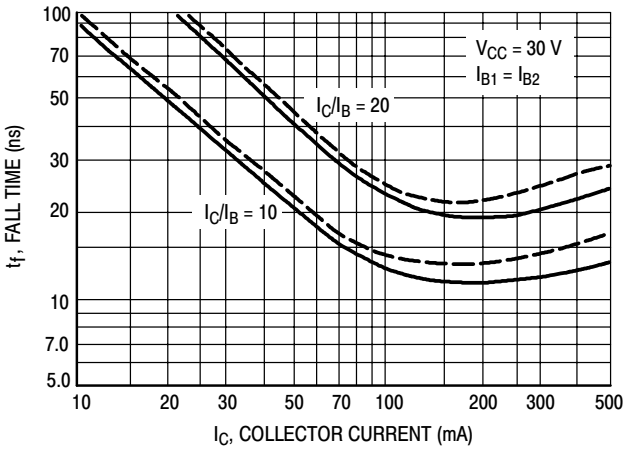


Figure 8. Fall Time

SMALL−SIGNAL CHARACTERISTICS

NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C; Bandwidth = 1.0 Hz

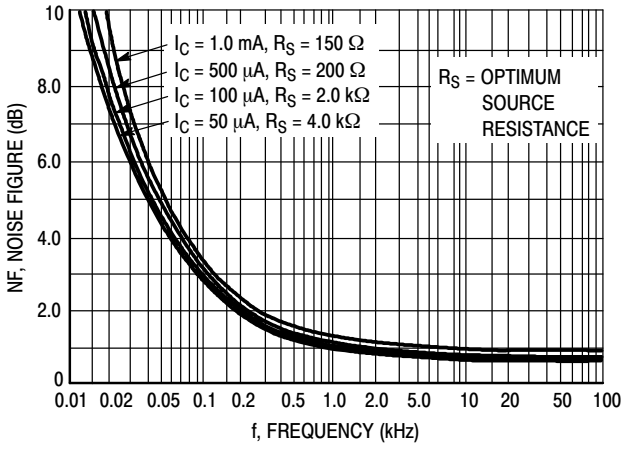


Figure 9. Frequency Effects

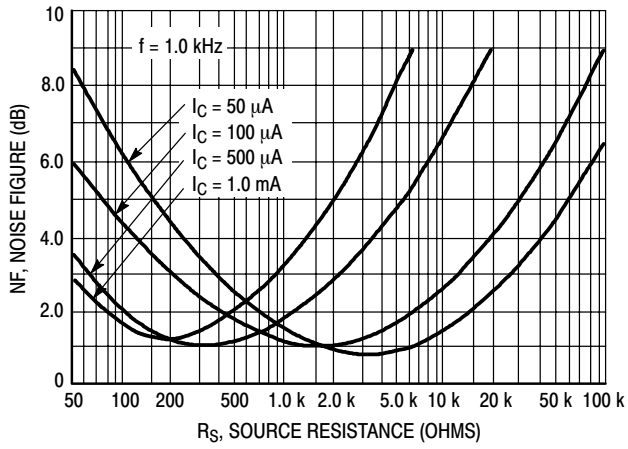


Figure 10. Source Resistance Effects

2N4401

h PARAMETERS

V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C

This group of graphs illustrates the relationship between h_{fe} and other “h” parameters for this series of transistors. To obtain these curves, a high−gain and a low−gain unit were selected from the 2N4401 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

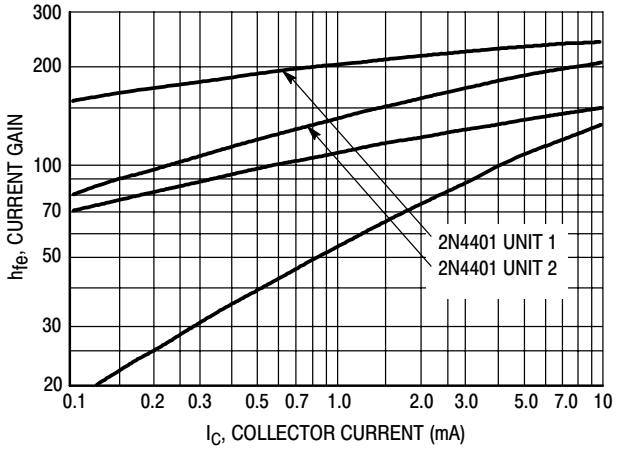


Figure 11. Current Gain

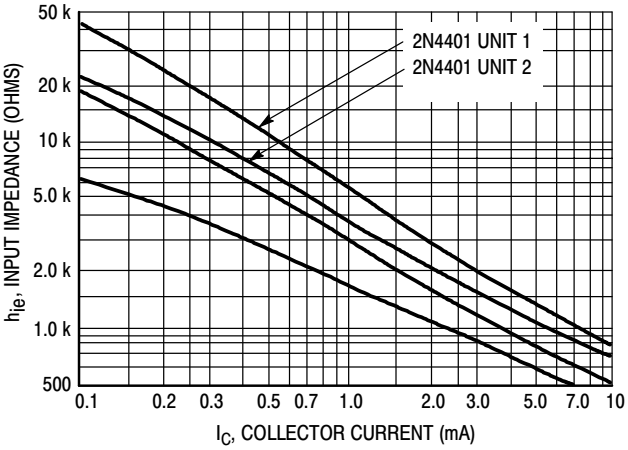


Figure 12. Input Impedance

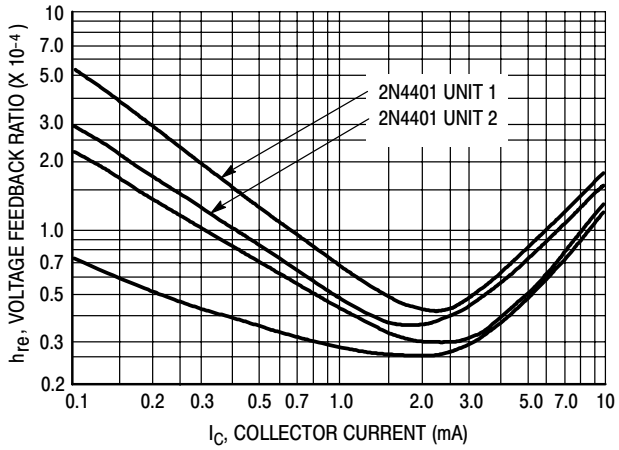


Figure 13. Voltage Feedback Ratio

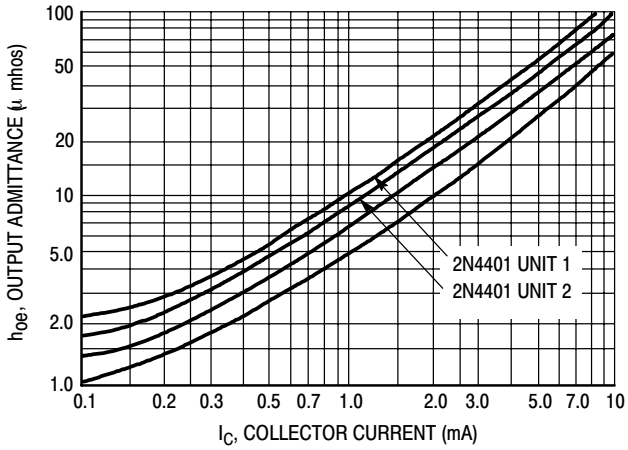


Figure 14. Output Admittance

2N4401

STATIC CHARACTERISTICS

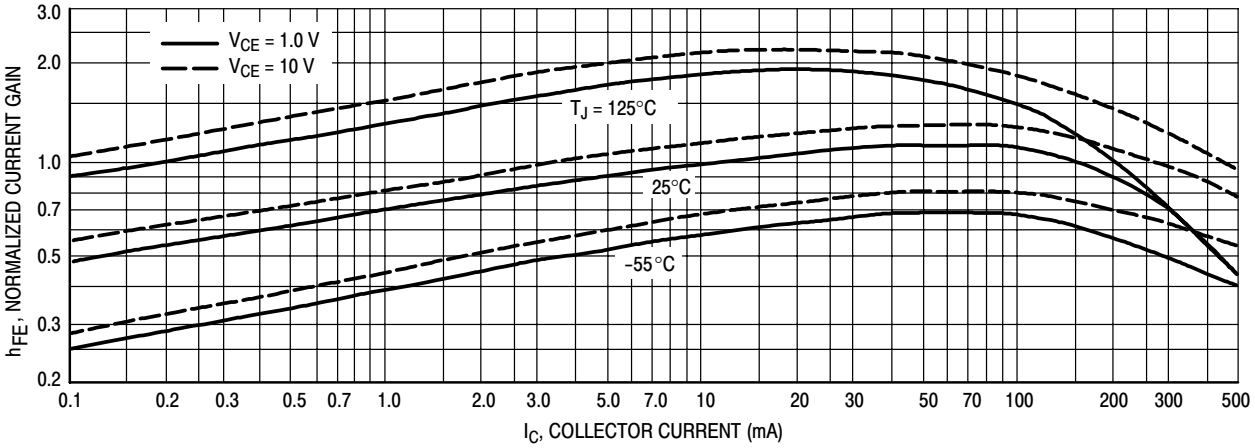


Figure 15. DC Current Gain

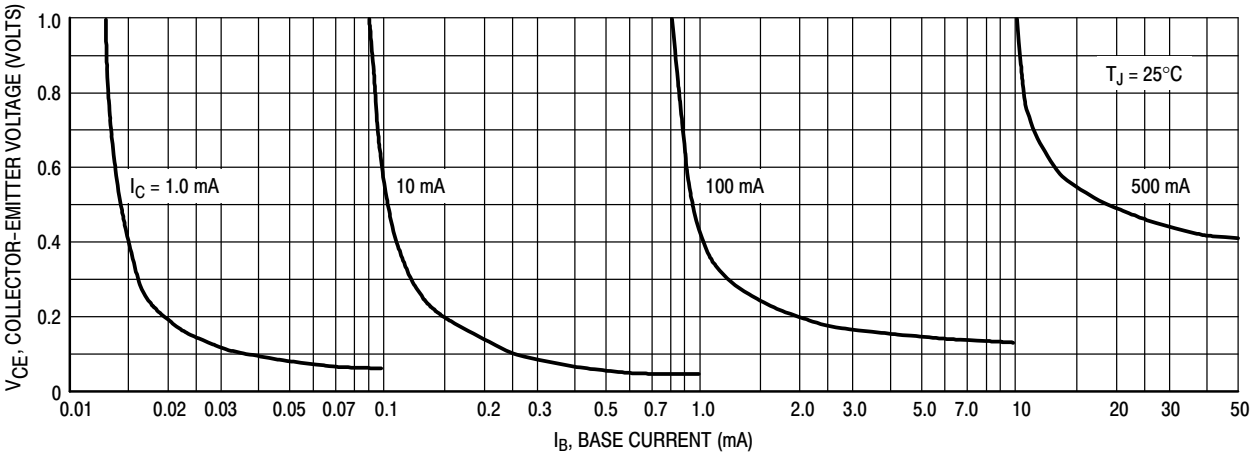


Figure 16. Collector Saturation Region

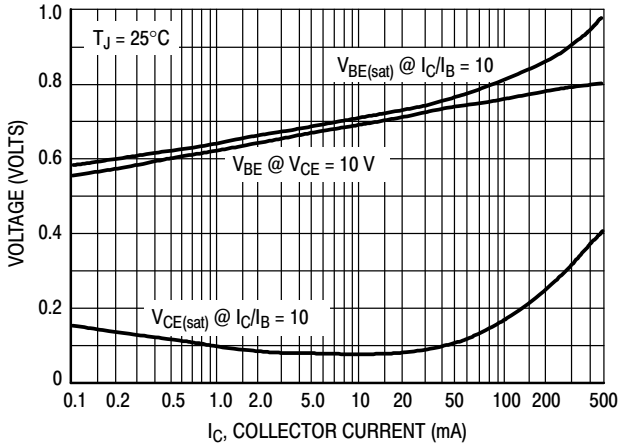


Figure 17. “On” Voltages

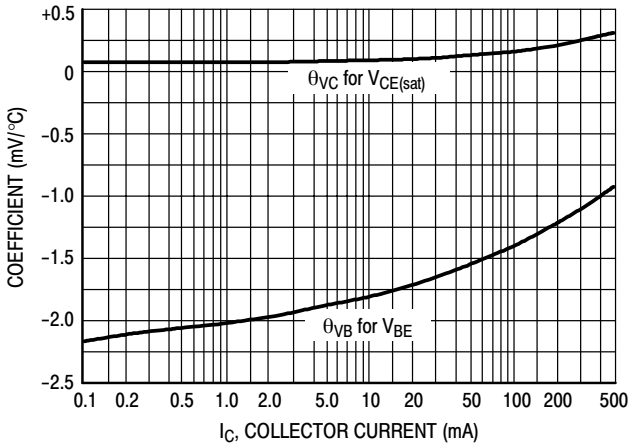
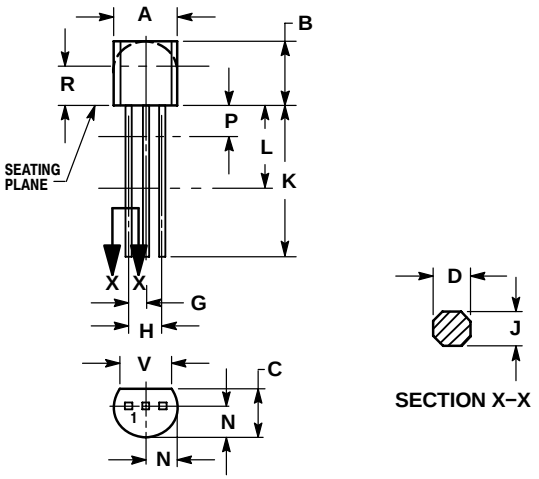


Figure 18. Temperature Coefficients

2N4401

PACKAGE DIMENSIONS

TO−92
TO−226AA
CASE 29−11
ISSUE AL



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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